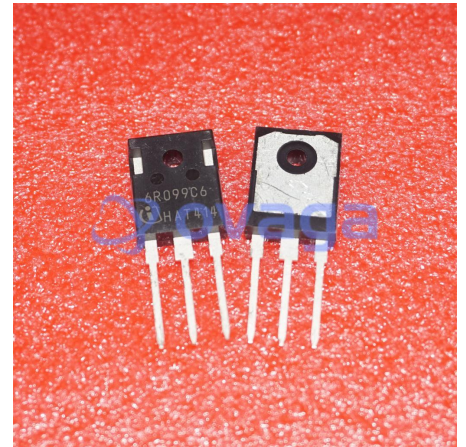


N-Channel MOSFETs (>500V...900V); Package: PG-TO247-3; VDS (max): 600.0 V; RDS(ON) @ TJ=25°C VGS=10: 99.0 mOhm; ID(max) @ TC=25°C: 38.0 A; IDpuls (max): 112.0 A;

Manufacturers	<a href="#">Infineon Technologies Corporation</a>
Package/Case	TO-247
Product Type	Transistors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for IPW60R099C6 or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

## General Description

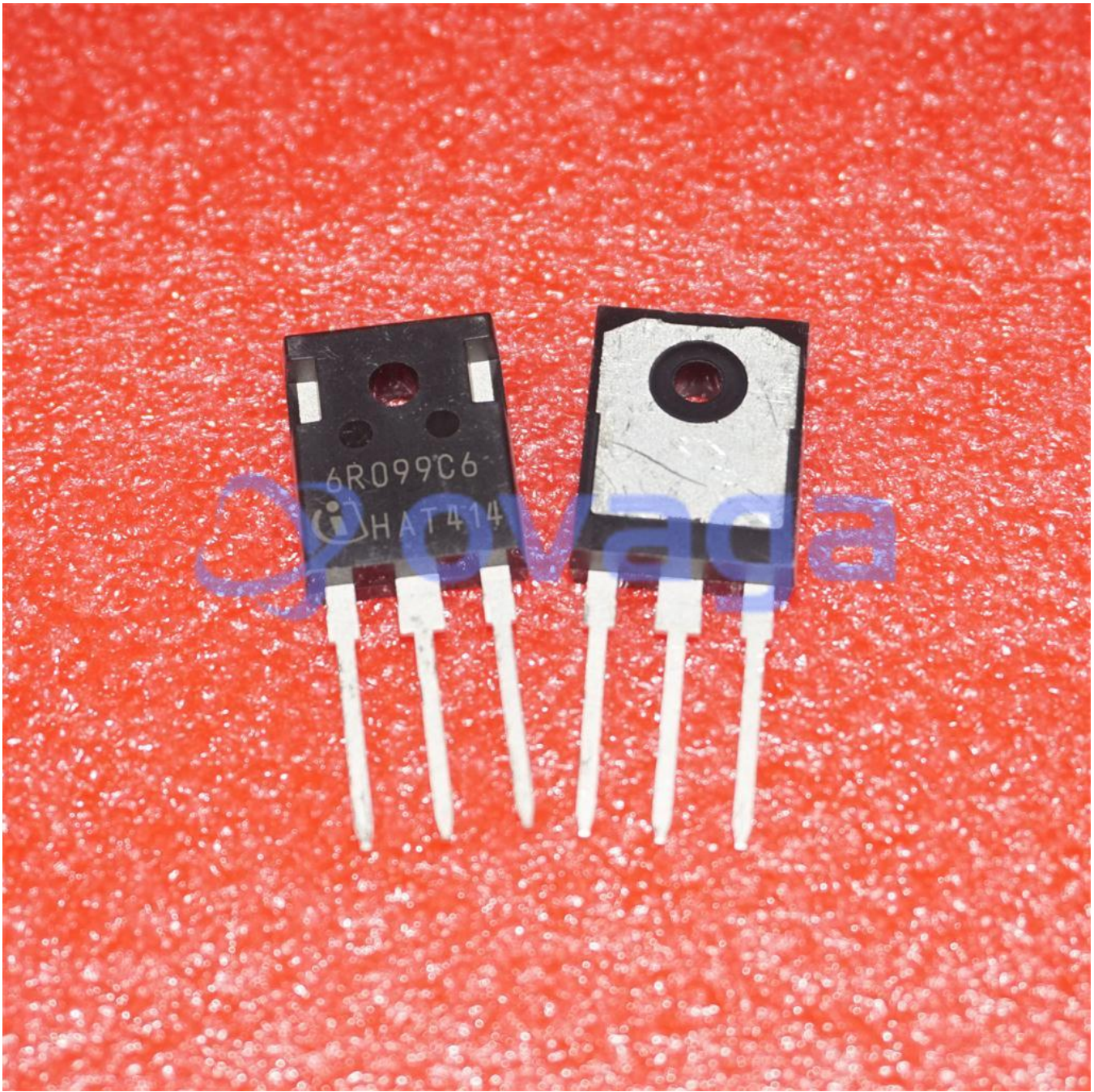
IPW60R099C6 is a power MOSFET (Metal Oxide Semiconductor Field Effect Transistor) designed and manufactured by Infineon Technologies AG. It is a high voltage N-channel MOSFET with a maximum voltage rating of 600V and a maximum current rating of 24A.

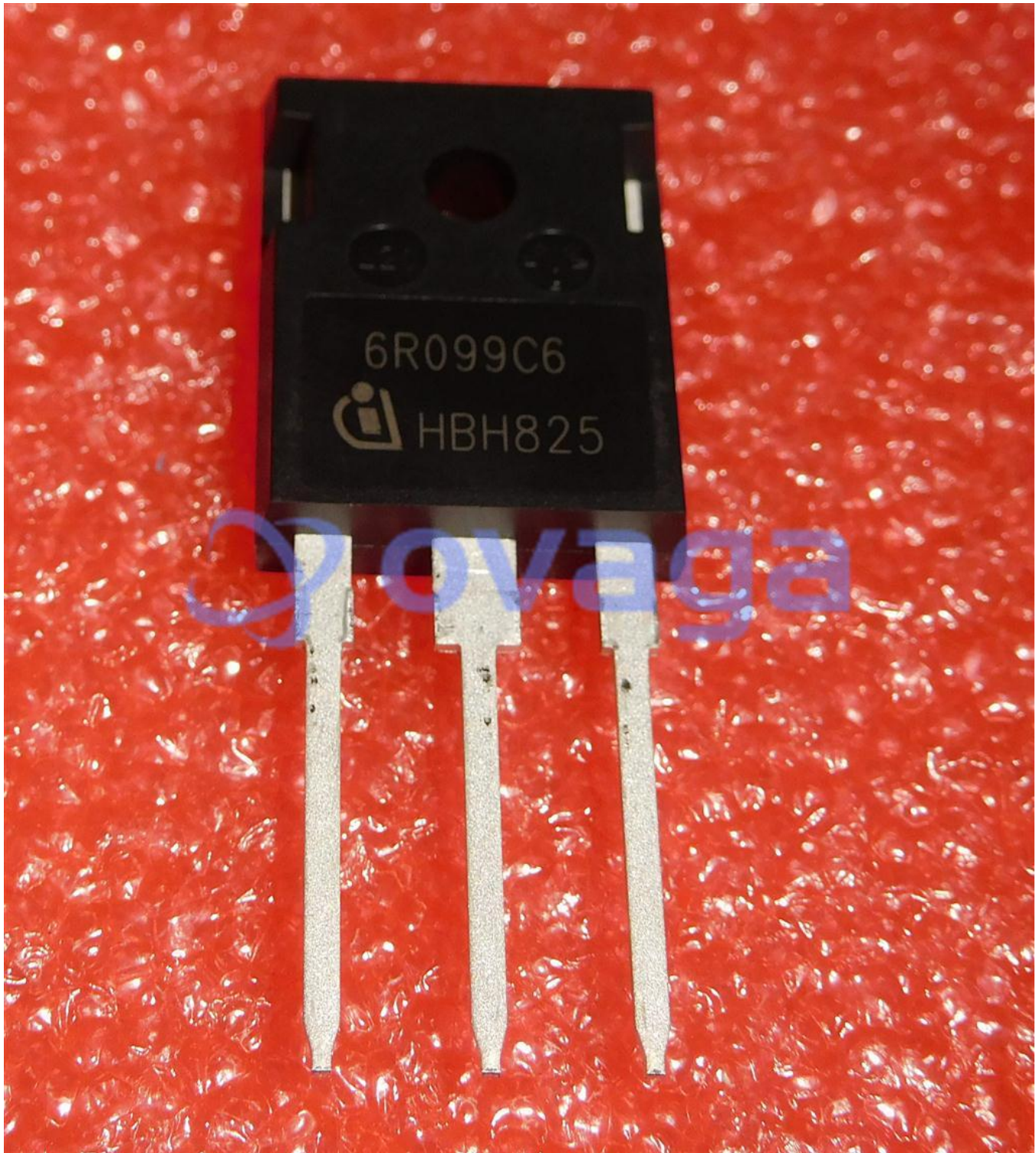
## Features

- Low on-state resistance (Rds(on)) of 0.099 ohms
- Fast switching speed and low gate charge
- Avalanche energy rating of 480 mJ
- TO-247 package with isolated mounting hole

## Application

- STP24NF06L
- FDPF24N60NZ
- IRFP240
- IXFK24N60P
- MTP24N60E





### Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation  
TO-220-3



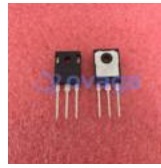
[IPB180N06S4-H1](#)

Infineon Technologies Corporation  
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation  
TDSON-8



[IPW65R080CFD](#)

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TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation  
PG-TO252-3



[IPD180N10N3G](#)

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TO-252



[IPP60R074C6](#)

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[IPD70R1K4P7S](#)

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TO252-3